Transistors

2.5V Drive Nch MOSFET RTL035N03

Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT6).
- 3) Low voltage drive (2.5V drive).

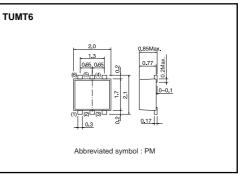
Applications

Switching

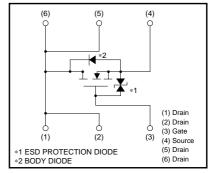
Packaging specifications

	Package	Taping	
Туре	Code	TR	
	Basic ordering unit (pieces)	3000	
RTL035N03		0	

•Dimensions (Unit : mm)



Inner circuit



•Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	30	V	
Gate-source voltage		V _{GSS}	12	V	
Drain current	Continuous	ID	±3.5	А	
Drain current	Pulsed	I _{DP} *1	±14	А	
Source current	Continuous	ls	0.8	А	
(Body diode)	Pulsed	Isp *1	14	А	
Total power dissipation		P _D *2	1.0	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	
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*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

*2 Mounted on a ceramic boar

•Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W
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* Mounted on a ceramic board



Transistors

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	10	μA	Vgs=12V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	_	V	I _D = 1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	-	-	1	μA	V _{DS} = 30V, V _{GS} =0V	
Gate threshold voltage	VGS (th)	0.5	-	1.5	V	V _{DS} = 10V, I _D = 1mA	
Static drain-source on-state resistance	RDS (on)*	-	40	56	mΩ	I _D = 3.5A, V _{GS} = 4.5V	
		-	42	59	mΩ	I _D =3.5A, V _{GS} = 4V	
resistance		-	56	79	mΩ	I _D = 3.5A, V _{GS} = 2.5V	
Forward transfer admittance	Y _{fs} *	3	-	_	S	V _{DS} = 10V, I _D = 3.5A	
Input capacitance	Ciss	-	350	_	pF	V _{DS} = 10V	
Output capacitance	Coss	-	90	_	pF	Vgs=0V	
Reverse transfer capacitance	Crss	-	55	_	pF	f=1MHz	
Turn-on delay time	t _{d (on)} *	-	9	_	ns	Vdd≒ 15V	
Rise time	tr *	-	25	_	ns	$I_{D}=1.75A$	
Turn-off delay time	td (off) *	_	32	-	ns	Vgs= 4.5V R∟=8.6Ω	
Fall time	t _f *	-	20	-	ns	$R_{G}=10\Omega$	
Total gate charge	Qg *	-	4.6	6.4	nC	V _{DD} ≒15V V _{GS} =4.5V	
Gate-source charge	Qgs *	-	0.8	-	nC	ID= 3.5A	
Gate-drain charge	Q _{gd} *	-	1.5	_	nC	RL=4.3Ω RG=10Ω	

•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd		-	1.2	V	Is= 0.8A, V _{GS} =0V

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